

MOSFET
OptiMOS™ 6 Power-Transistor, 120 V

Features

- N-channel, normal level
- Very low on-resistance R_DS(on)
- Excellent gate charge x R_DS(on) product (FOM)
- Very low reverse recovery charge (Q_rr)
- High avalanche energy rating
- 175°C operating temperature
- Optimized for high frequency switching
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21
- MSL 1 classified according to J-STD-020

Product validation

Fully qualified according to JEDEC for Industrial Applications

Table 1 Key Performance Parameters

Table with 3 columns: Parameter, Value, Unit. Rows include V_DS (120 V), R_DS(on),max (2.6 mΩ), I_D (224 A), Q_oss (166 nC), Q_G (0V...10V) (70 nC), and Q_rr (1000A/μs) (245 nC).

Table with 4 columns: Type/Ordering Code, Package, Marking, Related Links. Row 1: IPT026N12NM6, PG-HSOF-8, 026N12N6, -

TOLL

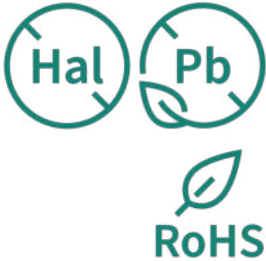
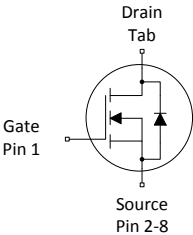
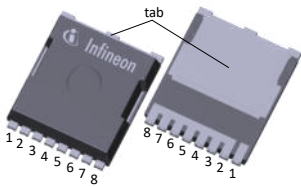




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1 Maximum ratings

at $T_A=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	224 158 144 23	A	$V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$ $V_{GS}=10\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=8\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=10\text{ V}$, $T_A=25\text{ °C}$, $R_{thJA}=50\text{ °C/W}$ ²⁾
Pulsed drain current ³⁾	$I_{D,pulse}$	-	-	896	A	$T_C=25\text{ °C}$
Avalanche current, single pulse ⁴⁾	I_{AS}	-	-	115	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse	E_{AS}	-	-	623	mJ	$I_D=62\text{ A}$, $R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	283 3.0	W	$T_C=25\text{ °C}$ $T_A=25\text{ °C}$, $R_{thJA}=50\text{ °C/W}$ ²⁾
Operating and storage temperature	T_j , T_{stg}	-55	-	175	°C	-

¹⁾ Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

³⁾ See Diagram 3 for more detailed information

⁴⁾ See Diagram 13 for more detailed information

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	0.53	°C/W	-
Thermal resistance, junction - ambient, 6 cm ² cooling area ⁵⁾	R_{thJA}	-	-	50	°C/W	-

⁵⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

3 Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	120	-	-	V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2.6	3.1	3.6	V	$V_{DS}=V_{GS}$, $I_D=169\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	0.1 10	1 100	μA	$V_{DS}=100\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$ $V_{DS}=100\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}$
Gate-source leakage current	I_{GSS}	-	10	100	nA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	2.2 2.5	2.6 3.13	m Ω	$V_{GS}=10\text{ V}$, $I_D=115\text{ A}$ $V_{GS}=8\text{ V}$, $I_D=58\text{ A}$
Gate resistance	R_G	0.5	1.0	1.5	Ω	-
Transconductance	g_{fs}	85	170	-	S	$ V_{DS} \geq 2 I_D $, $R_{DS(on)max}$, $I_D=115\text{ A}$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	5000	6500	pF	$V_{GS}=0\text{ V}$, $V_{DS}=60\text{ V}$, $f=1\text{ MHz}$
Output capacitance ⁶⁾	C_{oss}	-	1500	2000	pF	$V_{GS}=0\text{ V}$, $V_{DS}=60\text{ V}$, $f=1\text{ MHz}$
Reverse transfer capacitance ⁶⁾	C_{rss}	-	27	47	pF	$V_{GS}=0\text{ V}$, $V_{DS}=60\text{ V}$, $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	17.1	-	ns	$V_{DD}=60\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=58\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Rise time	t_r	-	9.7	-	ns	$V_{DD}=60\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=58\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	28.0	-	ns	$V_{DD}=60\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=58\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Fall time	t_f	-	11.7	-	ns	$V_{DD}=60\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=58\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$

⁶⁾ Defined by design. Not subject to production test.

Table 6 Gate charge characteristics ⁷⁾

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Gate to source charge ⁸⁾	Q_{gs}	-	26	34	nC	$V_{DD}=60\text{ V}$, $I_D=58\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge at threshold ⁸⁾	$Q_{g(th)}$	-	15.5	19.4	nC	$V_{DD}=60\text{ V}$, $I_D=58\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge ⁸⁾	Q_{gd}	-	15.4	23	nC	$V_{DD}=60\text{ V}$, $I_D=58\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Switching charge	Q_{sw}	-	26	-	nC	$V_{DD}=60\text{ V}$, $I_D=58\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total ⁸⁾	Q_g	-	70	88	nC	$V_{DD}=60\text{ V}$, $I_D=58\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	5.1	-	V	$V_{DD}=60\text{ V}$, $I_D=58\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Output charge ⁸⁾	Q_{oss}	-	166	221	nC	$V_{DS}=60\text{ V}$, $V_{GS}=0\text{ V}$

⁷⁾ See "Gate charge waveforms" for parameter definition

⁸⁾ Defined by design. Not subject to production test.

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	224	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	896	A	$T_C=25\text{ °C}$
Diode forward voltage	V_{SD}	-	0.87	1.0	V	$V_{GS}=0\text{ V}$, $I_F=115\text{ A}$, $T_J=25\text{ °C}$
Reverse recovery time ⁹⁾	t_{rr}	-	35	70	ns	$V_R=60\text{ V}$, $I_F=58\text{ A}$, $di_F/dt=300\text{ A}/\mu\text{s}$
Reverse recovery charge ⁹⁾	Q_{rr}	-	85	170	nC	$V_R=60\text{ V}$, $I_F=58\text{ A}$, $di_F/dt=300\text{ A}/\mu\text{s}$
Reverse recovery time ⁹⁾	t_{rr}	-	30	60	ns	$V_R=60\text{ V}$, $I_F=58\text{ A}$, $di_F/dt=1000\text{ A}/\mu\text{s}$
Reverse recovery charge ⁹⁾	Q_{rr}	-	245	490	nC	$V_R=60\text{ V}$, $I_F=58\text{ A}$, $di_F/dt=1000\text{ A}/\mu\text{s}$

⁹⁾ Defined by design. Not subject to production test.

4 Electrical characteristics diagrams

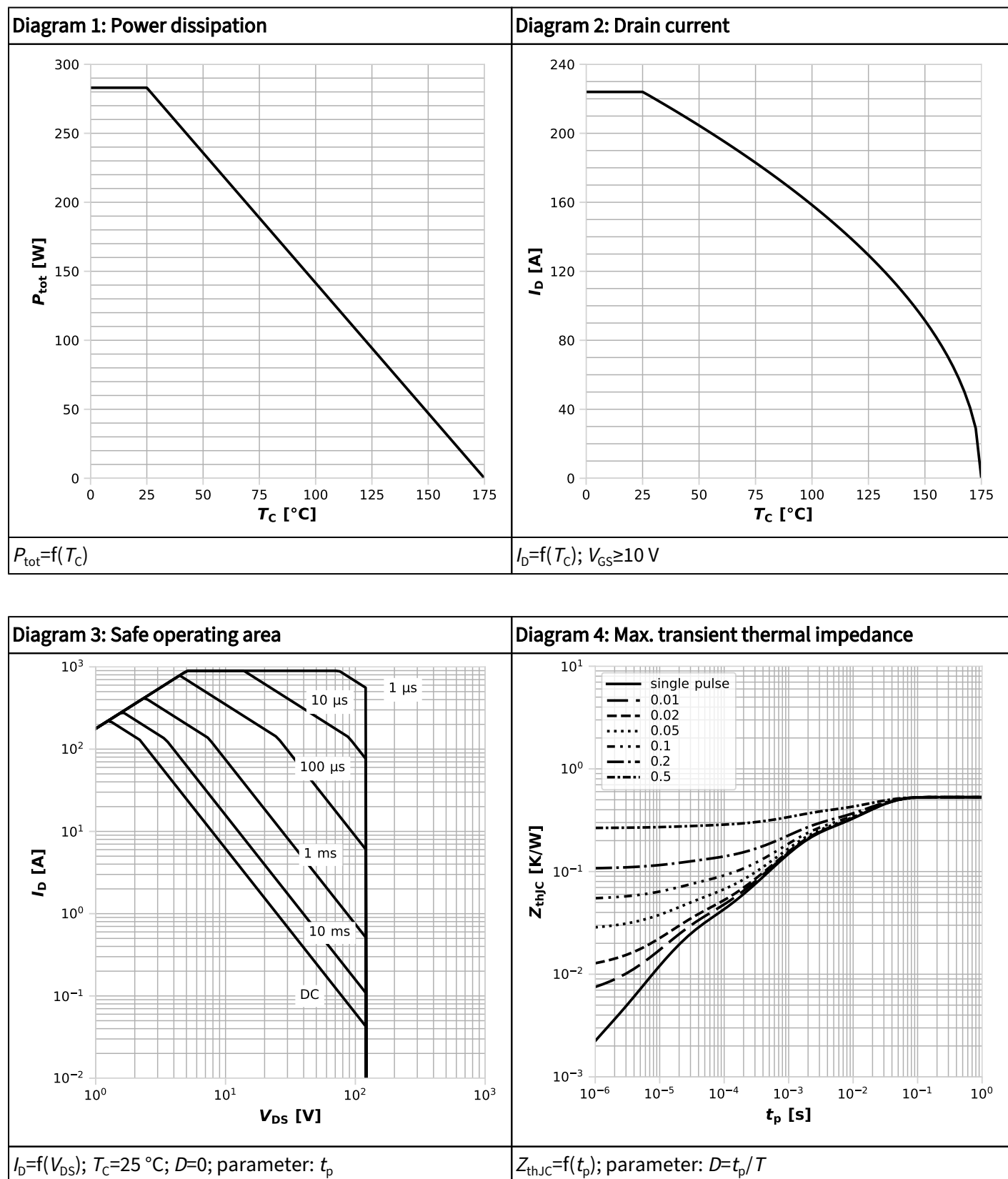
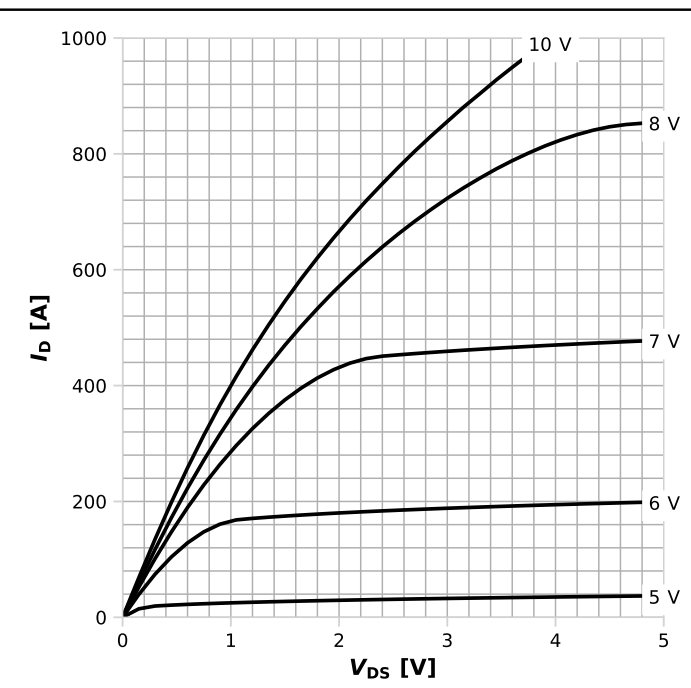
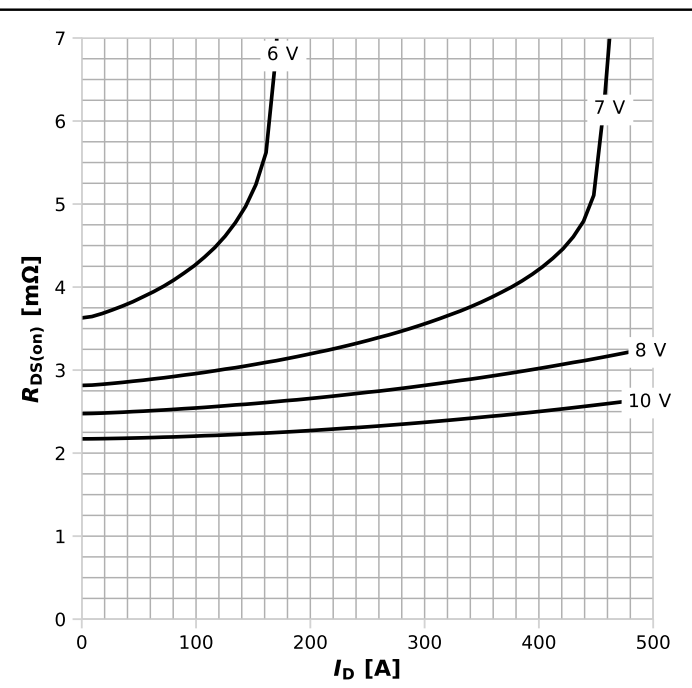


Diagram 5: Typ. output characteristics



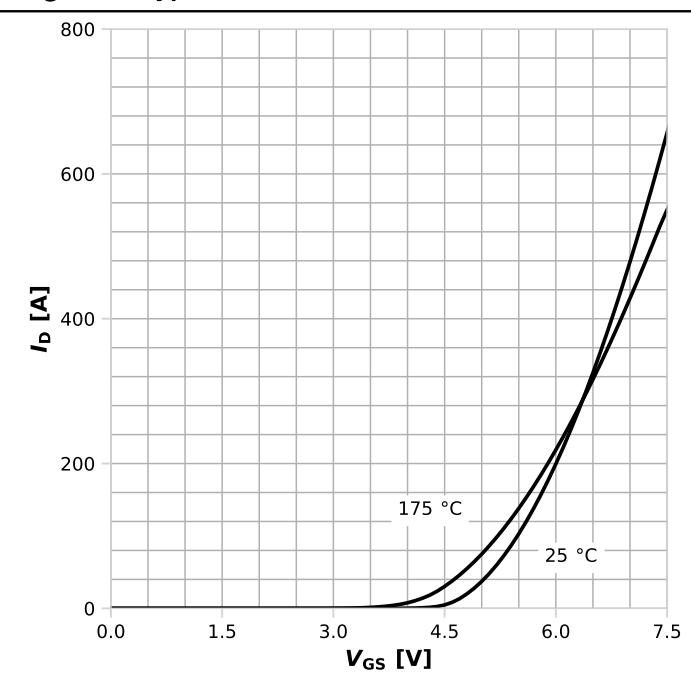
$I_D = f(V_{DS})$, $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



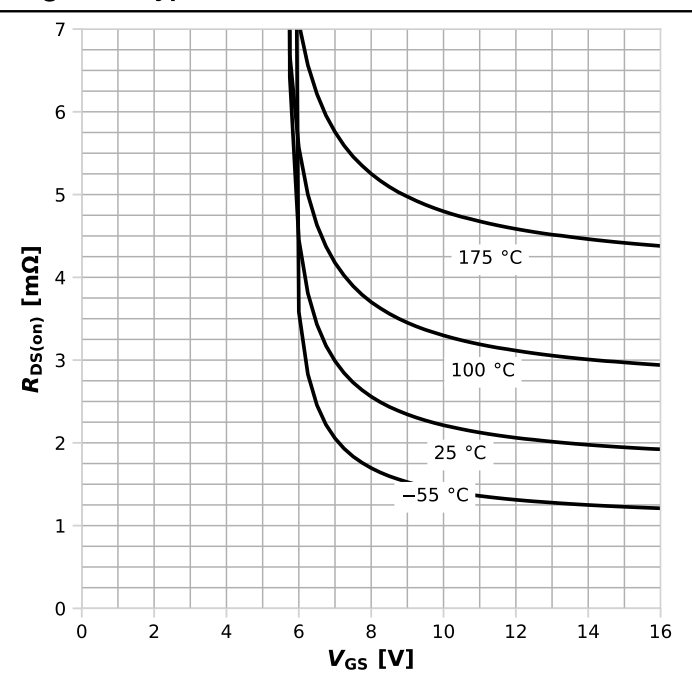
$R_{DS(on)} = f(I_D)$, $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



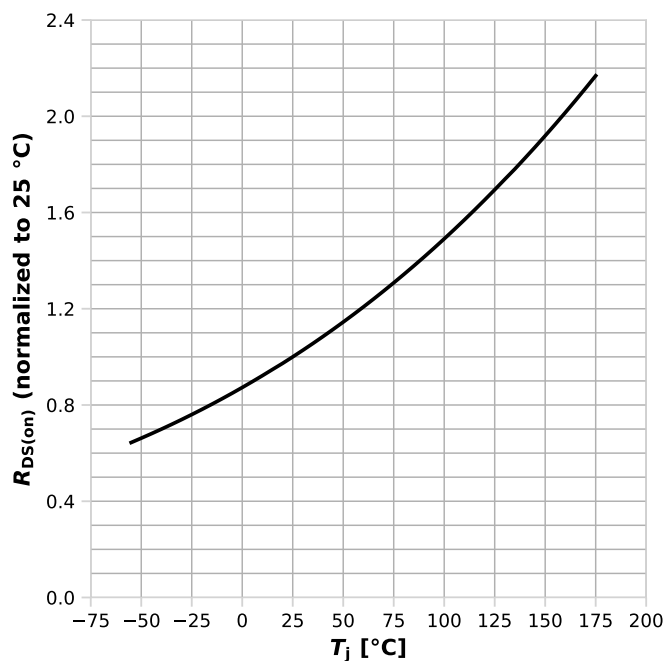
$I_D = f(V_{GS})$, $|V_{DS}| > 2|I_D|R_{DS(on)\max}$; parameter: T_j

Diagram 8: Typ. drain-source on resistance



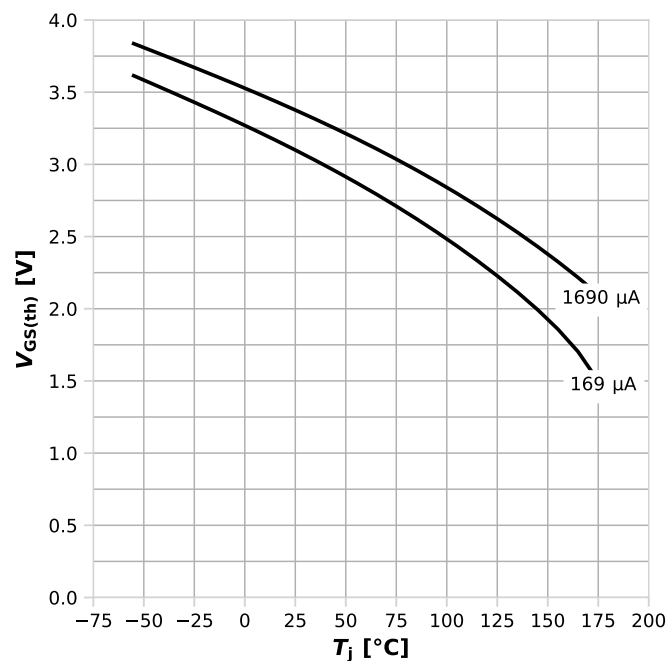
$R_{DS(on)} = f(V_{GS})$, $I_D = 115\text{ A}$; parameter: T_j

Diagram 9: Normalized drain-source on resistance



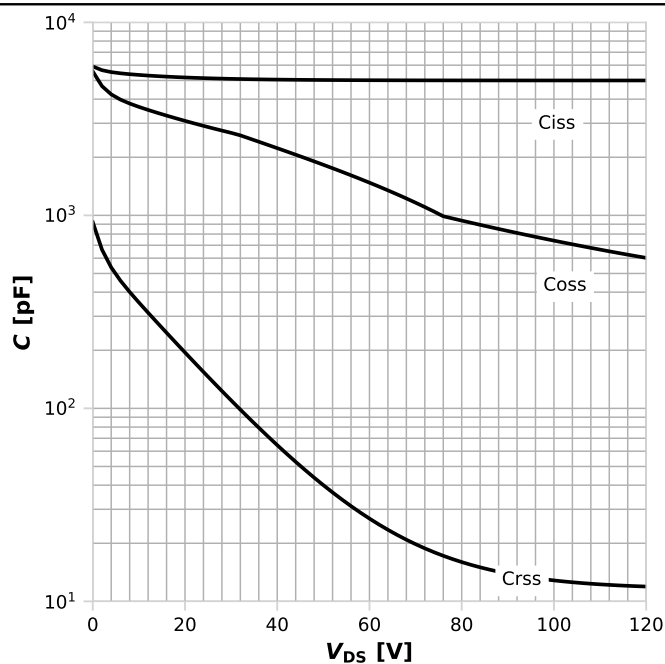
$$R_{DS(on)} = f(T_j), I_D = 115 \text{ A}, V_{GS} = 10 \text{ V}$$

Diagram 10: Typ. gate threshold voltage



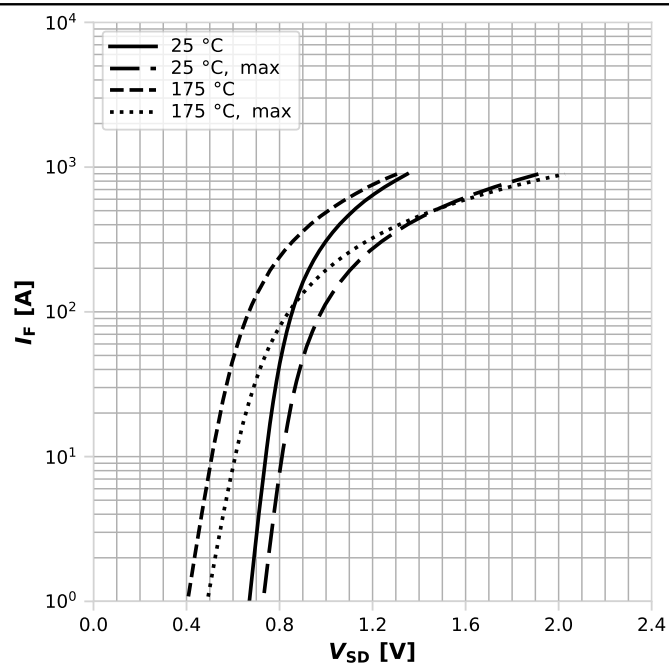
$$V_{GS(th)} = f(T_j), V_{GS} = V_{DS}; \text{ parameter: } I_D$$

Diagram 11: Typ. capacitances

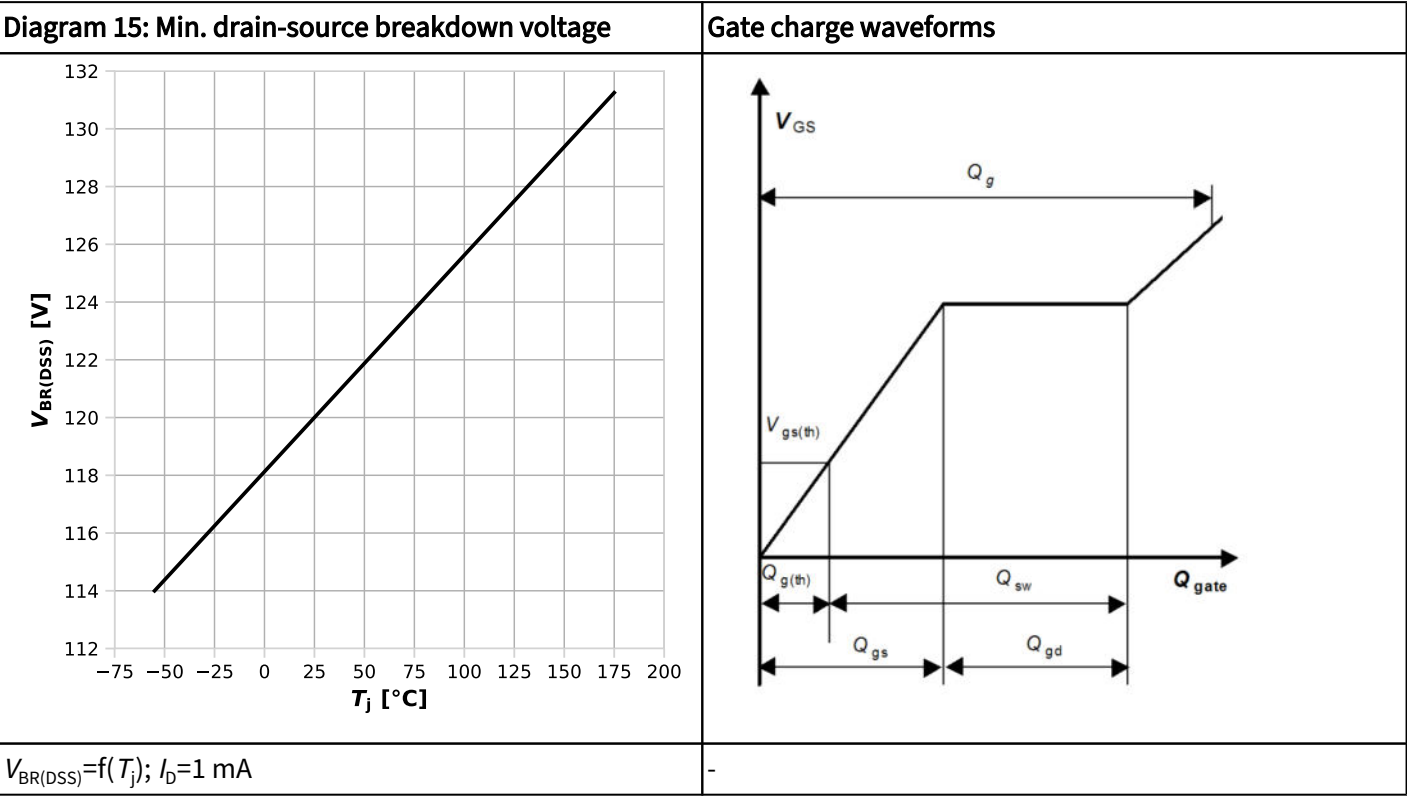
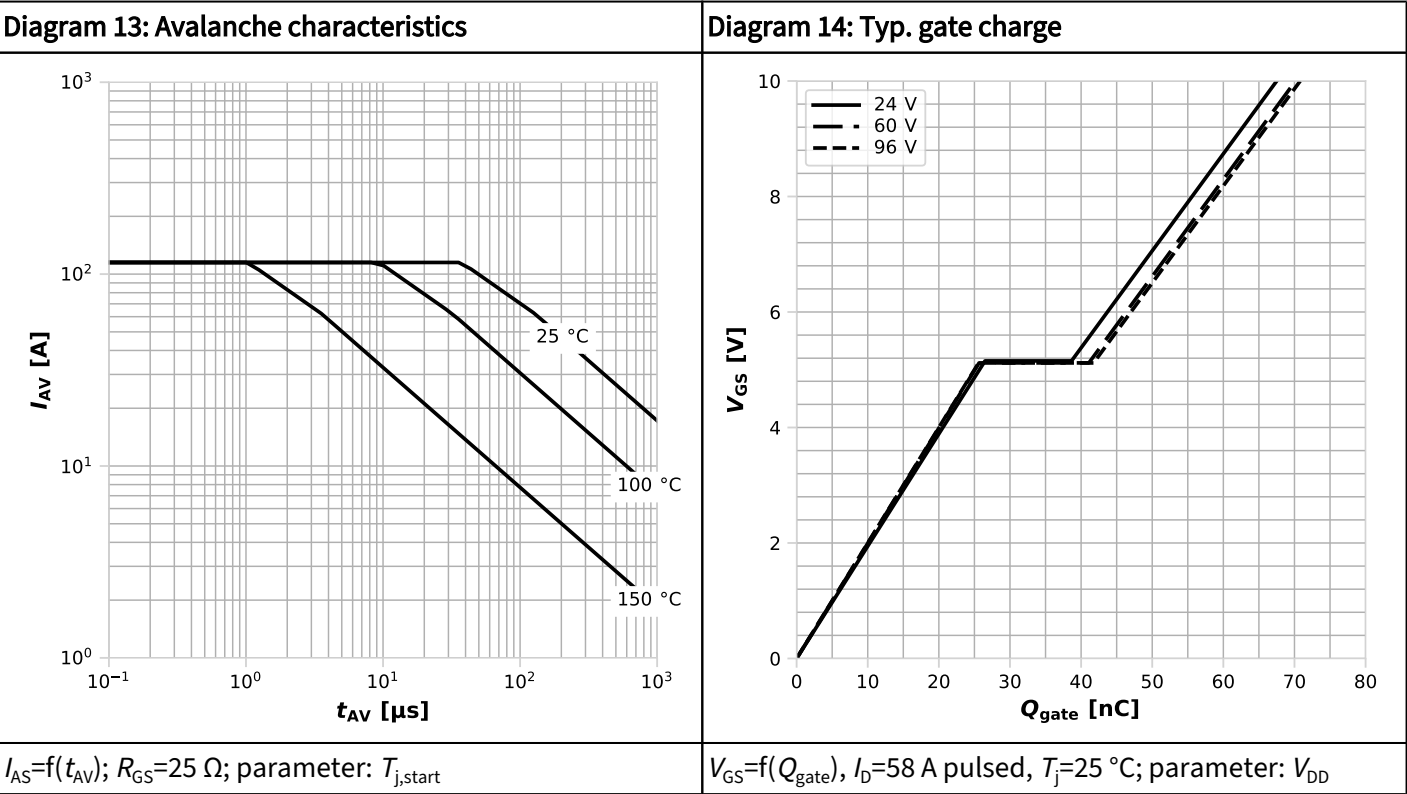


$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$

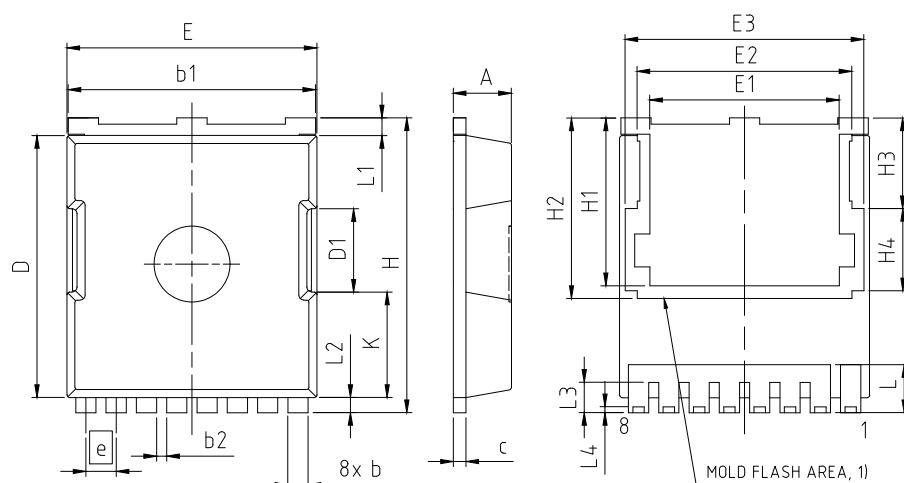
Diagram 12: Forward characteristics of reverse diode



$$I_F = f(V_{SD}); \text{ parameter: } T_j$$

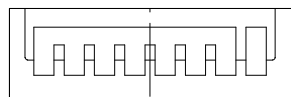


5 Package Outlines



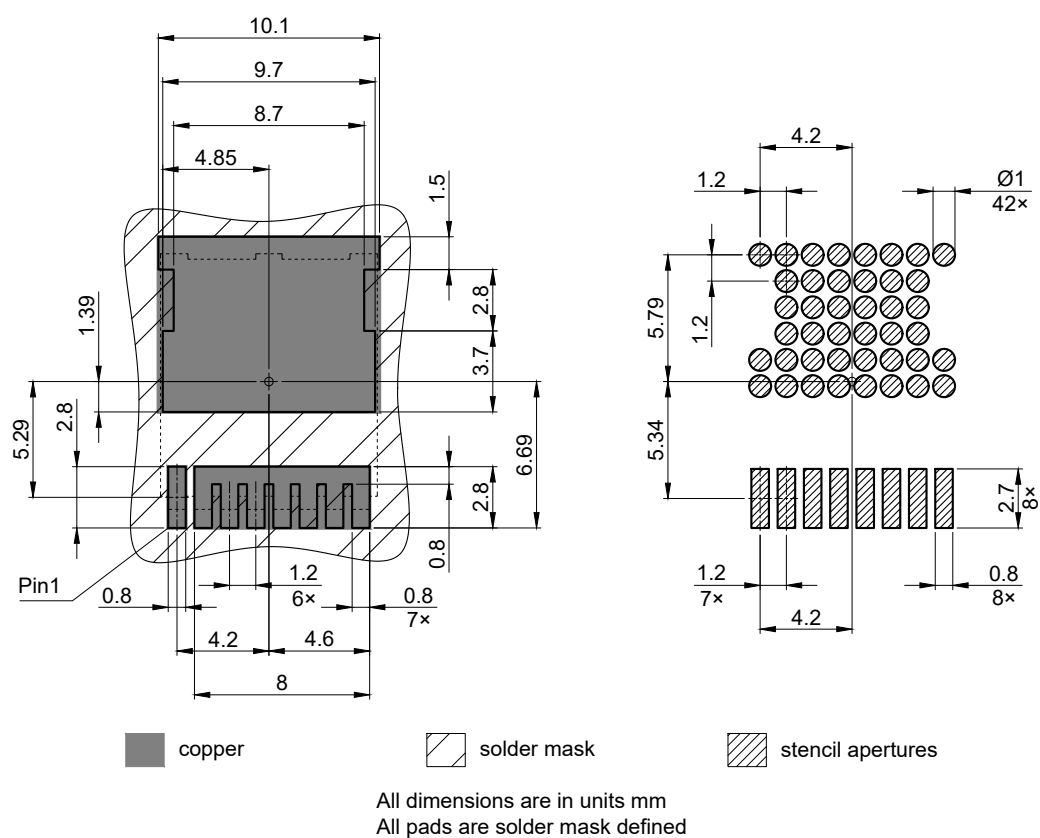
PACKAGE - GROUP NUMBER: PG-HSOF-8-U01		
DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	2.20	2.40
b	0.70	0.90
b1	9.70	9.90
b2	0.42	0.50
c	0.40	0.60
D	10.28	10.58
D1	3.30	
E	9.70	10.10
E1	7.50	
E2	8.50	
E3	9.46	
e	1.20 (BSC)	
H	11.48	11.88
H1	6.55	6.95
H2	7.15	
H3	3.59	
H4	3.26	
N	8	
K	4.18	
L	1.60	2.10
L1	0.50	0.90
L2	0.50	0.70
L3	1.00	1.30
L4	0.13	0.33

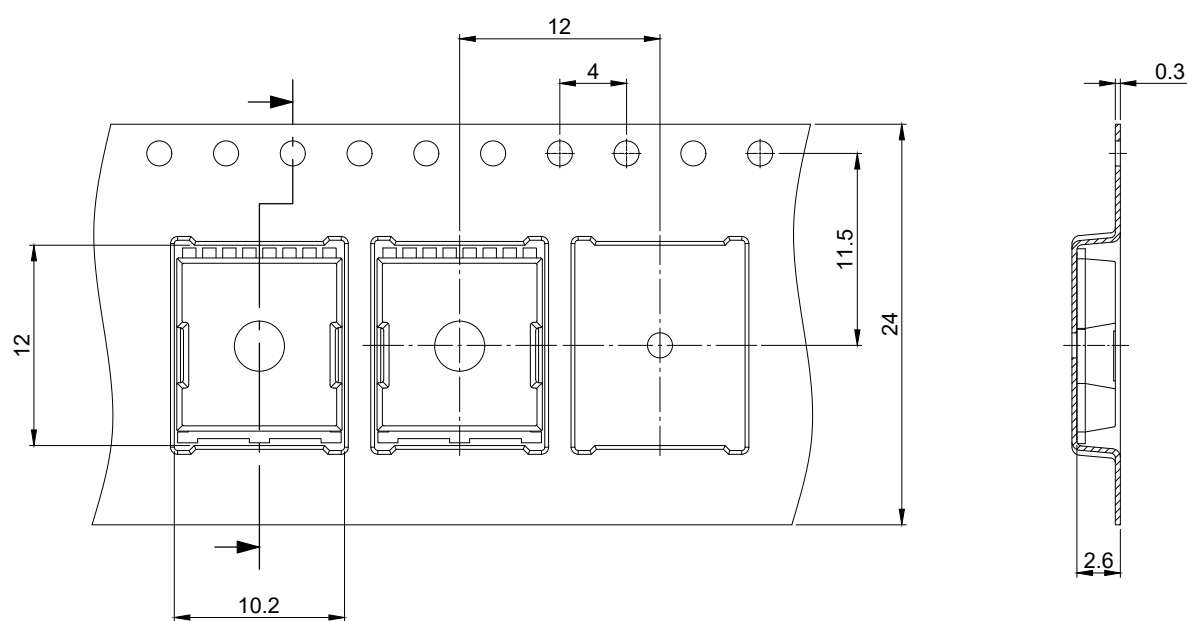
5:1


 OPTIONAL LEAD FORM:
 WITHOUT LTI OPTION

1) PATIALLY COVERED WITH MOLD FLASH

Figure 1 Outline PG-HSOF-8, dimensions in mm


Figure 2 Outline PG-HSOF-8, dimensions in mm



All dimensions are in units mm

The drawing is in compliance with ISO 128-30, Projection Method 1 []

Figure 3 Outline PG-HSOF-8, dimensions in mm

Revision History

IPT026N12NM6

Revision 2024-07-29, Rev. 1.0

Previous Revision

Revision	Date	Subjects (major changes since last revision)
1.0	2024-07-29	Release of final datasheet

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